

#### 40V 175°C N-CHANNEL ENHANCEMENT MODE MOSFET

## **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	Q <sub>g</sub> Typ	I <sub>D</sub> T <sub>C</sub> = +25°C (Note 10)
40V	3mΩ @ V <sub>GS</sub> = 10V	68.6nC	100A

#### **Features**

- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped inductive switching ensures more reliable and robust end application
- Low R<sub>DS(ON)</sub> Minimizes Power Losses
- Low Q<sub>g</sub> Minimizes Switching Losses
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

## **Description and Applications**

This MOSFET is designed to meet the stringent requirements of Automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

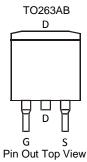
- Engine Management Systems
- Body Control Electronics
- DC-DC Converters

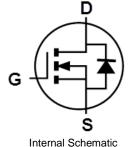
#### **Mechanical Data**

- Case: TO263AB
- Case Material: Molded Plastic, "Green" Molding Compound; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish Matte Tin Annealed over Copper Leadframe.
   Solderable per MIL-STD-202, Method 208 
   3
- Weight: 1.7 grams (Approximate)



Top View





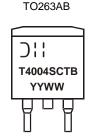
## **Ordering Information (Note 5)**

Part Number	Case	Packaging
DMTH4004SCTBQ-13	TO263AB	800/Tape & Reel

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. For more information, please refer to http://www.diodes.com/product\_compliance\_definitions.html.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

# **Marking Information**



T4004SCTB = Product Type Marking Code YYWW = Date Code Marking YY = Last Two Digits of Year (ex: 14 = 2014) WW = Week (01 to 53)



# **Maximum Ratings** ( $@T_A = +25^{\circ}C$ , unless otherwise specified.)

Characteristic	Symbol	Value	Units	
Drain-Source Voltage	$V_{DSS}$	40	V	
Gate-Source Voltage	$V_{GSS}$	±20	V	
Continuous Drain Current (Note 7)	T <sub>C</sub> = +25°C (Note 10)	I <sub>D</sub>	100	А
·	$T_{C} = +100^{\circ}C$		100	
Maximum Continuous Body Diode Forward Current		Is	100	Α
Pulsed Drain Current (10µs pulse, duty cycle = 1%)		I <sub>DM</sub>	200	Α
Avalanche Current, L=0.2mH		I <sub>AS</sub>	45	Α
Avalanche Energy, L=0.2mH		E <sub>AS</sub>	200	mJ

## **Thermal Characteristics**

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 6)	T <sub>A</sub> = +25°C	$P_{D}$	4.7	W
Thermal Resistance, Junction to Ambient (Note 6)		$R_{\theta JA}$	32	°C/W
Total Power Dissipation (Note 7) $T_C = +25^{\circ}C$		P <sub>D</sub>	136	W
Thermal Resistance, Junction to Case (Note 7)		$R_{\theta JC}$	1.1	°C/W
Operating and Storage Temperature Range		T <sub>J,</sub> T <sub>STG</sub>	-55 to +175	°C

# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	40	_	_	V	$V_{GS} = 0V$ , $I_D = 1mA$
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_	_	1	μΑ	$V_{DS} = 32V, V_{GS} = 0V$
Gate-Source Leakage	$I_{GSS}$	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	$V_{GS(TH)}$	2	_	4	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	_	2.5	3	mΩ	$V_{GS} = 10V, I_D = 100A$
Diode Forward Voltage	$V_{SD}$	_	_	1.3	V	$V_{GS} = 0V, I_{S} = 100A$
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C <sub>iss</sub>	_	4,305	_	рF	$V_{DS} = 25V$ , $V_{GS} = 0V$ f = 1MHz
Output Capacitance	Coss	_	1,441	_		
Reverse Transfer Capacitance	Crss	_	102	_		
Gate Resistance	$R_{G}$	_	0.77	_	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$
Total Gate Charge	$Q_g$	_	68.6	_		$V_{DD} = 20V, I_D = 90A,$ $V_{GS} = 10V$
Gate-Source Charge	Qgs	_	16.8	_	nC	
Gate-Drain Charge	$Q_{gd}$	_	14.2	_		
Turn-On Delay Time	t <sub>D(ON)</sub>	_	9.5	_		$V_{DD} = 20V, V_{GS} = 10V,$ $I_{D} = 90A, R_{G} = 3.5\Omega$
Turn-On Rise Time	t <sub>R</sub>	_	6.7	_	ns	
Turn-Off Delay Time	t <sub>D(OFF)</sub>	_	26.4	_	115	
Turn-Off Fall Time	t <sub>F</sub>	_	8.1	_		
Reverse Recovery Time	t <sub>RR</sub>	_	52.4	_	ns	I_ 500 di/dt 1000/up
Reverse Recovery Charge	Q <sub>RR</sub>	_	78.2	_	nC	I <sub>F</sub> = 50A, di/dt = 100A/μs

Notes: 6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1-inch square copper plate. 7. Thermal resistance from junction to soldering point (on the exposed drain pad).

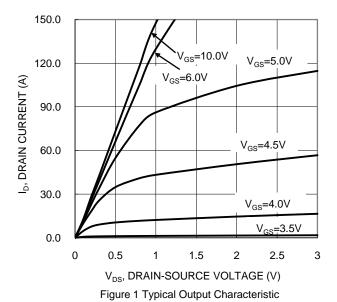
<sup>8.</sup> Short duration pulse test used to minimize self-heating effect.

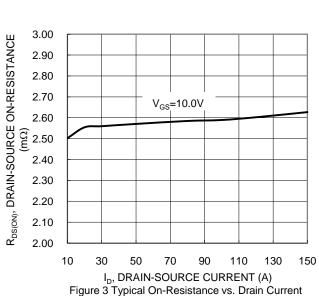
Guaranteed by design. Not subject to product testing.

<sup>10.</sup> Package limited.

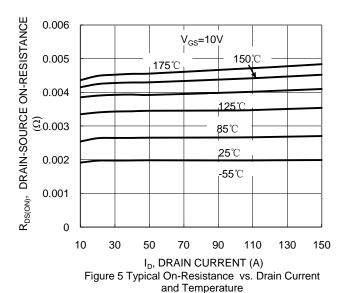


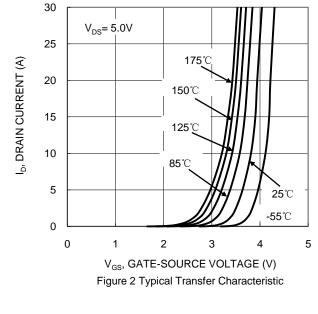


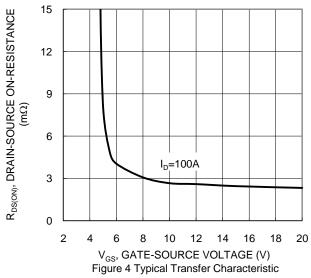


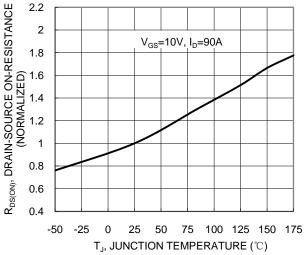


and Gate Voltage



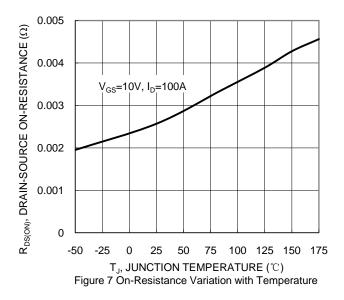


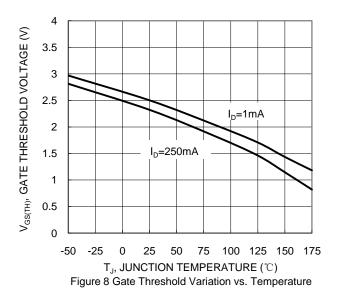


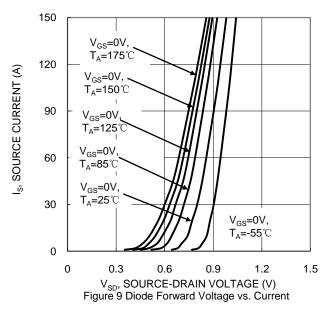


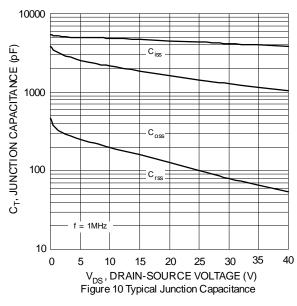


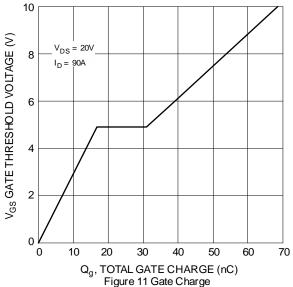


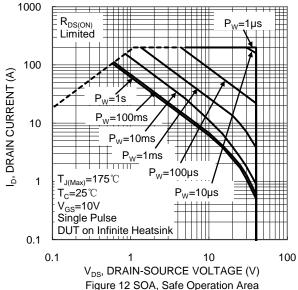




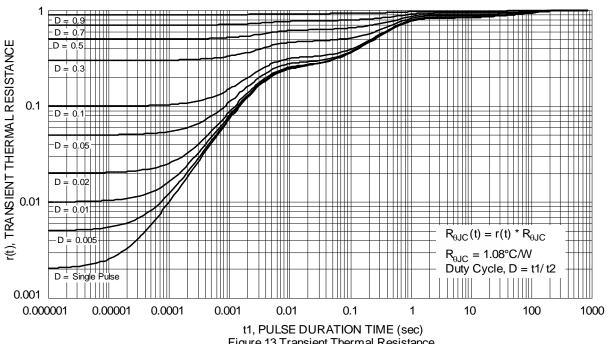










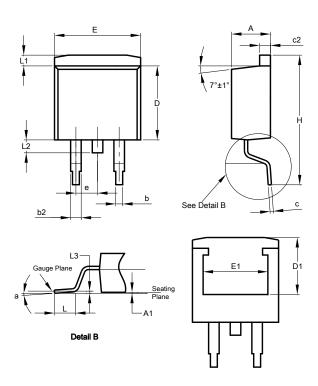




# **Package Outline Dimensions**

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.

### TO263AB (D2PAK)

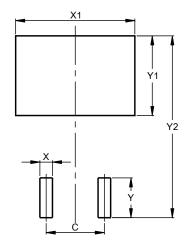


TO263AB (D2PAK)				
Dim	Min	Max	Тур	
Α	4.07	4.82	-	
A1	0.00	0.25	-	
b	0.51	0.99	-	
b2	1.15	1.77	-	
С	0.356	0.73	-	
c2	1.143	1.65	-	
D	8.39	9.65	-	
D1	6.55	6.95	-	
е		2.54 T\	/P	
Е	9.66	10.66	-	
E1	6.23	8.23	-	
Н	14.61	15.87	-	
L	1.78	2.79	-	
L1	-	1.67	-	
L2	-	1.77	-	
L3	-	-	0.254	
а	0°	8°	-	
All Dimensions in mm				

# **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.

### TO263AB (D2PAK)



Dimensions	Value (in mm)		
С	5.08		
Х	1.10		
X1	10.41		
Υ	3.50		
Y1	7.01		
Y2	15.99		



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